

Product Preview

Medium Power Surface Mount Products

TMOS Single P-Channel

Field Effect Transistor

Micro8™ devices are an advanced series of power MOSFETs which utilize Motorola's High Cell Density HDTMOS process to achieve lowest possible on-resistance per silicon area. They are capable of withstanding high energy in the avalanche and commutation modes and the drain-to-source diode has a very low reverse recovery time. Micro8™ devices are designed for use in low voltage, high speed switching applications where power efficiency is important. Typical applications are dc-dc converters, and power management in portable and battery powered products such as computers, printers, cellular and cordless phones. They can also be used for low voltage motor controls in mass storage products such as disk drives and tape drives. The avalanche energy is specified to eliminate the guesswork in designs where inductive loads are switched and offer additional safety margin against unexpected voltage transients.

- Miniature Micro8 Surface Mount Package — Saves Board Space
- Extremely Low Profile (<1.1 mm) for thin applications such as PCMCIA cards
- Ultra Low RDS(on) Provides Higher Efficiency and Extends Battery Life
- Logic Level Gate Drive — Can Be Driven by Logic ICs
- Diode Is Characterized for Use In Bridge Circuits
- Diode Exhibits High Speed, With Soft Recovery
- IDSS Specified at Elevated Temperature
- Avalanche Energy Specified
- Mounting Information for Micro8 Package Provided



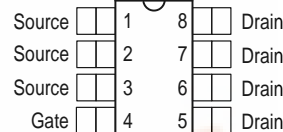
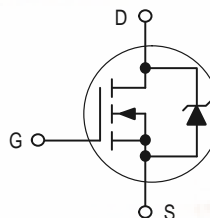
MTSF3203

Motorola Preferred Device

**SINGLE TMOS
 POWER MOSFET
 4.9 AMPERES
 20 VOLTS
 RDS(on) = 0.05 OHM**



**CASE 846A-02, Style 1
 Micro8**



Top View

DEVICE MARKING

ORDERING INFORMATION

3A	Device	Reel Size	Tape Width	Quantity
	MTSF3203R2	13"	12 mm embossed tape	4000 units

Preferred devices are Motorola recommended choices for future use and best overall value.

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MTSF3203

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating		Symbol	Max	Unit
Drain-to-Source Voltage		V_{DSS}	20	V
Drain-to-Gate Voltage ($R_{GS} = 1.0\text{ M}\Omega$)		V_{DGR}	20	V
Gate-to-Source Voltage — Continuous		V_{GS}	± 12	V
1 inch SQ. FR-4 or G-10 PCB Figure 1 below Steady State	Thermal Resistance — Junction to Ambient	R_{THJA}	70	$^\circ\text{C/W}$
	Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.79	Watts
	Linear Derating Factor		14.29	$\text{mW}/^\circ\text{C}$
	Drain Current — Continuous @ $T_A = 25^\circ\text{C}$	I_D	4.9	A
	Continuous @ $T_A = 70^\circ\text{C}$	I_D	3.9	A
	Pulsed Drain Current (1)	I_{DM}	24.4	A
Minimum FR-4 or G-10 PCB Figure 2 below Steady State	Thermal Resistance — Junction to Ambient	R_{THJA}	160	$^\circ\text{C/W}$
	Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	0.78	Watts
	Linear Derating Factor		6.25	$\text{mW}/^\circ\text{C}$
	Drain Current — Continuous @ $T_A = 25^\circ\text{C}$	I_D	3.2	A
	Continuous @ $T_A = 70^\circ\text{C}$	I_D	2.5	A
	Pulsed Drain Current (1)	I_{DM}	16	A
Operating and Storage Temperature Range		T_J, T_{Stg}	- 55 to 150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy — Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 30\text{ Vdc}$, $V_{GS} = 5.0\text{ Vdc}$, Peak $I_L = 4.9\text{ Apk}$, $L = \text{TBD mH}$, $R_G = 25\ \Omega$)		EAS	TBD	mJ

(1) Repetitive rating; pulse width limited by maximum junction temperature.

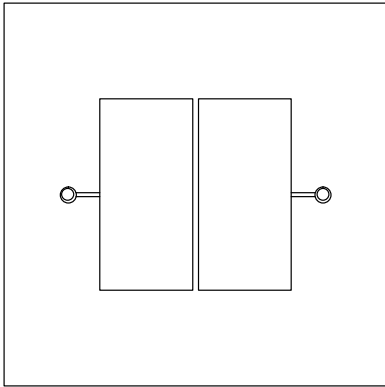


Figure 1. 1.0 Inch Square FR-4 or G-10 PCB

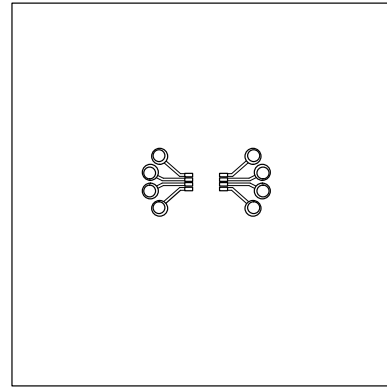


Figure 2. Minimum FR-4 or G-10 PCB

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\ \mu\text{Adc}$) Temperature Coefficient (Positive)	($C_{pk} \geq 2.0$) (1) (3) $V_{(BR)DSS}$	20 —	— TBD	— —	Vdc mV/°C
Zero Gate Voltage Drain Current ($V_{DS} = 20\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 20\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	I_{DSS}	— —	— —	1.0 25	μAdc
Gate-Body Leakage Current ($V_{GS} = \pm 12\text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	—	—	100	nAdc

ON CHARACTERISTICS(1)

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{Adc}$) Threshold Temperature Coefficient (Negative)	($C_{pk} \geq 2.0$) (3) $V_{GS(th)}$	1.0 —	TBD TBD	— —	Vdc mV/°C
Static Drain-to-Source On-Resistance ($V_{GS} = 4.5\text{ Vdc}$, $I_D = 4.9\text{ Adc}$) ($V_{GS} = 2.5\text{ Vdc}$, $I_D = 3.9\text{ Adc}$)	($C_{pk} \geq 2.0$) (3) $R_{DS(on)}$	— —	TBD TBD	40 50	m Ω
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 4.9\text{ Adc}$)	g_{FS}	2.0	—	—	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = 16\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{iss}	—	TBD	—	pF
Output Capacitance		C_{oss}	—	TBD	—	
Transfer Capacitance		C_{rss}	—	TBD	—	

SWITCHING CHARACTERISTICS(2)

Turn-On Delay Time	$(V_{DS} = 10\text{ Vdc}$, $I_D = 4.9\text{ Adc}$, $V_{GS} = 4.5\text{ Vdc}$, $R_G = 6\ \Omega$) (1)	$t_{d(on)}$	—	TBD	—	ns
Rise Time		t_r	—	TBD	—	
Turn-Off Delay Time		$t_{d(off)}$	—	TBD	—	
Fall Time		t_f	—	TBD	—	
Turn-On Delay Time	$(V_{DD} = 10\text{ Vdc}$, $I_D = 3.9\text{ Adc}$, $V_{GS} = 2.5\text{ Vdc}$, $R_G = 6\ \Omega$) (1)	$t_{d(on)}$	—	TBD	—	ns
Rise Time		t_r	—	TBD	—	
Turn-Off Delay Time		$t_{d(off)}$	—	TBD	—	
Fall Time		t_f	—	TBD	—	
Gate Charge	$(V_{DS} = 10\text{ Vdc}$, $I_D = 4.9\text{ Adc}$, $V_{GS} = 4.5\text{ Vdc}$)	Q_T	—	TBD	TBD	nC
		Q_1	—	TBD	—	
		Q_2	—	TBD	—	
		Q_3	—	TBD	—	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	$(I_S = 1.5\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$) (1) $(I_S = 1.5\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	V_{SD}	— —	TBD TBD	1.0 —	Vdc
Reverse Recovery Time	$(I_S = 1.5\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $di_S/dt = 100\text{ A}/\mu\text{s}$) (1)	t_{rr}	—	TBD	—	ns
		t_a	—	TBD	—	
		t_b	—	TBD	—	
Reverse Recovery Storage Charge		Q_{RR}	—	TBD	—	μC

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

(3) Reflects typical values. $C_{pk} = \left| \frac{\text{Max limit} - \text{Typ}}{3 \times \text{SIGMA}} \right|$

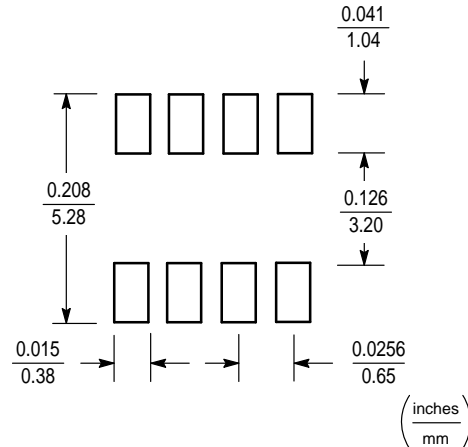
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INFORMATION FOR USING THE Micro8 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to ensure proper solder connection interface

between the board and the package. With the correct pad geometry, the packages will self-align when subjected to a solder reflow process.



Micro8 POWER DISSIPATION

The power dissipation of the Micro8 is a function of the input pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient; and the operating temperature, T_A . Using the values provided on the data sheet for the Micro8 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into

the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 0.78 Watts.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{160^\circ\text{C/W}} = 0.78 \text{ Watts}$$

The 160°C/W for the Micro8 package assumes the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 0.78 Watts using the footprint shown. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using board material such as Thermal Clad, the power dissipation can be doubled using the same footprint.

SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.

- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones and a figure for belt speed. Taken together, these control settings make up a heating "profile" for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 3 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems, but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time. The

line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joints.

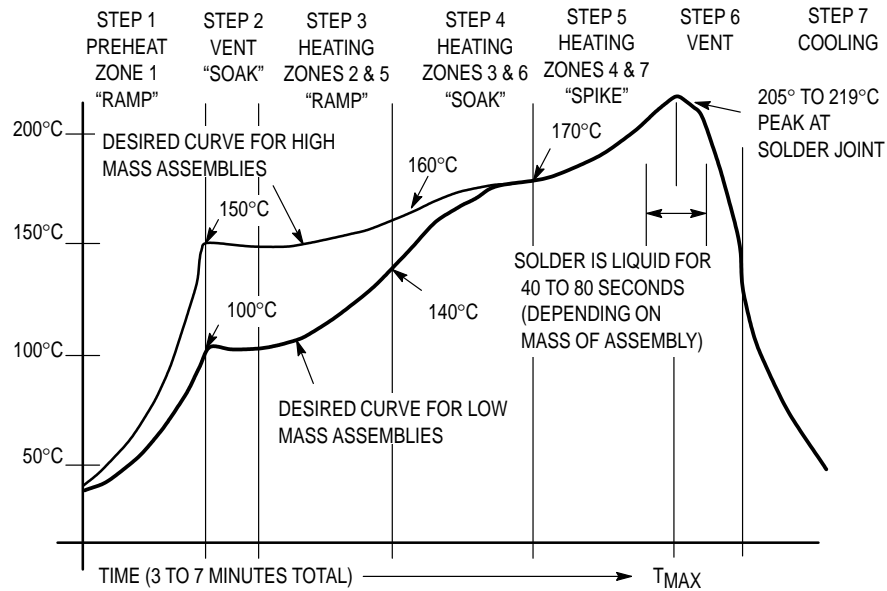


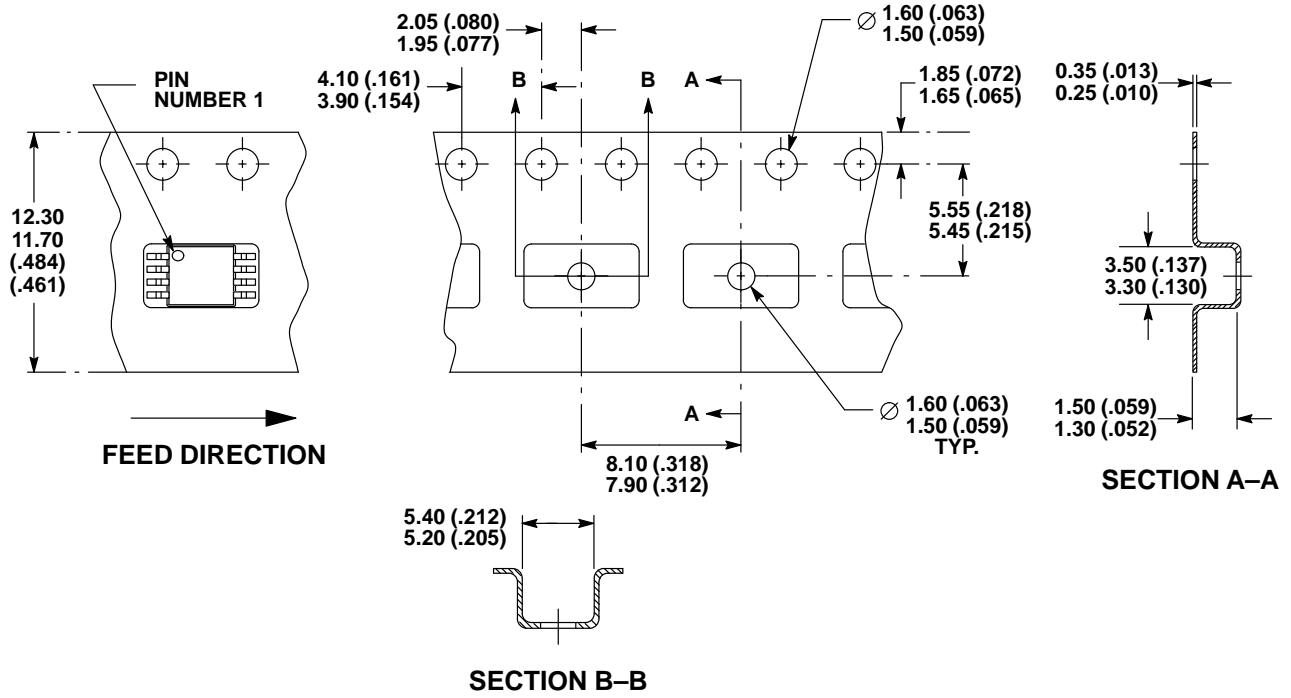
Figure 3. Typical Solder Heating Profile

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TAPE & REEL INFORMATION

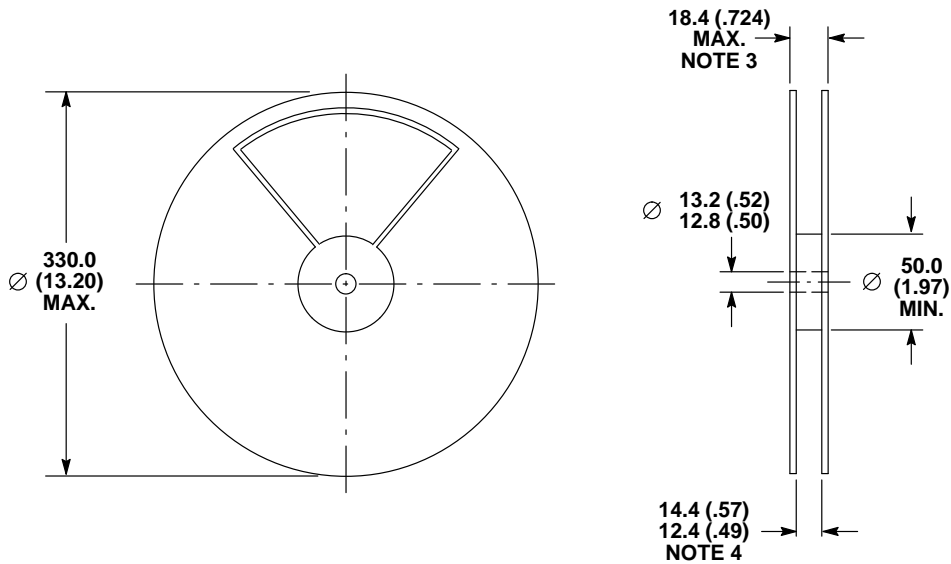
Micro8

Dimensions are shown in millimeters (inches)



NOTES:

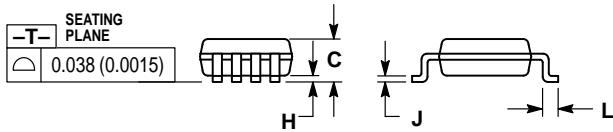
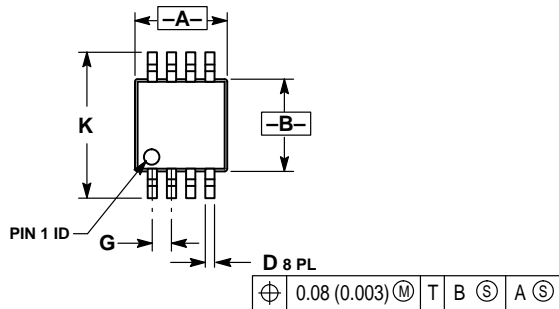
1. CONFORMS TO EIA-481-1.
2. CONTROLLING DIMENSION: MILLIMETER.



NOTES:

1. CONFORMS TO EIA-481-1.
2. CONTROLLING DIMENSION: MILLIMETER.
3. INCLUDES FLANGE DISTORTION AT OUTER EDGE.
4. DIMENSION MEASURED AT INNER HUB.

PACKAGE DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	—	1.10	—	0.043
D	0.25	0.40	0.010	0.016
G	0.65 BSC		0.026 BSC	
H	0.05	0.15	0.002	0.006
J	0.13	0.23	0.005	0.009
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

CASE 846A-02
ISSUE D
MICRO8

MTSF3203

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